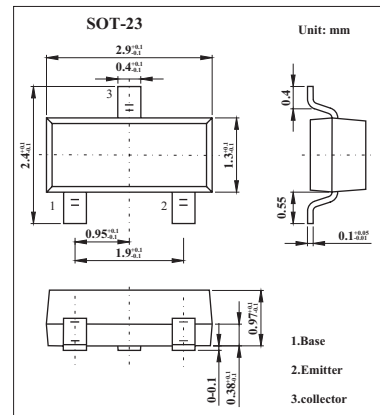


BC856,BC857,BC858

■ Features

- Low current (max. 100 mA).
- Low voltage (max. 65 V).



■ Absolute Maximum Ratings Ta = 25°C

| Parameter | Symbol | BC856 | BC857 | BC858 | Unit |
|---|---------------------|-------------|-------|-------|------|
| Collector-base voltage | V _{CBO} | -80 | -50 | -30 | V |
| Collector-emitter voltage | V _{CEO} | -65 | -45 | -30 | V |
| Emitter-base voltage | V _{EB0} | -5 | | | V |
| Collector current | I _C | -100 | | | mA |
| Peak collector current | I _{CM} | -200 | | | mA |
| Peak base current | I _{BM} | -200 | | | mA |
| Total power dissipation * | P _{tot} | 250 | | | mW |
| Junction temperature | T _j | 150 | | | °C |
| Storage temperature | T _{stg} | -65 to +150 | | | °C |
| Operating ambient temperature | R _{amb} | -65 to +150 | | | °C |
| Thermal resistance from junction to ambient * | R _{th j-a} | 500 | | | K/W |

* Transistor mounted on an FR4 printed-circuit board, standard footprint.

BC856,BC857,BC858

■ Electrical Characteristics Ta = 25°C

| Parameter | | Symbol | Testconditons | Min | Typ | Max | Unit |
|--------------------------------------|----------------------|----------------------|--|------|------|------|------|
| Collector cutoff current | | ICBO | V _{CB} = -30 V, I _E = 0 | | -1 | -15 | nA |
| | | ICBO | V _{CB} = -30 V, I _E = 0, T _j = 150°C | | | -4 | μA |
| Emitter cutoff current | | IEBO | V _{EB} = -5 V, I _C = 0 | | | -100 | nA |
| DC current gain | BC856 | hFE | I _C = -2 mA; V _{CE} = -5 V | | 125 | 475 | |
| | BC857 | | | | 125 | 800 | |
| | BC856A,BC857A | | | | 125 | 250 | |
| | BC856B,BC857B,BC858B | | | | 220 | 475 | |
| | BC857C | | | | 420 | 800 | |
| Collector-emitter saturation voltage | | V _{CE(sat)} | I _C = -10 mA; I _B = -0.5 mA | | -75 | -300 | mV |
| | | | I _C = -100 mA; I _B = -5 mA; * | | -250 | -650 | mV |
| Base-emitter saturation voltage | | V _{BE(sat)} | I _C = -10 mA; I _B = -0.5 mA | | -700 | | mV |
| | | | I _C = -100 mA; I _B = -5 mA; * | | -850 | | mV |
| Base-emitter voltage | | V _{BE} | I _C = -2 mA; V _{CE} = -5 V | -600 | -650 | -750 | mV |
| | | | I _C = -10 mA; V _{CE} = -5 V | | | -820 | mV |
| Collector capacitance | | C _C | V _{CB} = -10 V; I _E = I _C = 0; f = 1 MHz | | 4.5 | | pF |
| Transition frequency | | f _T | V _{CE} = -5 V; I _C = -10 mA; f = 100 MHz | 100 | | | MHz |
| Noise figure | | NF | I _C = -200 μA; V _{CE} = -5 V; R _S = 2 kΩ; f = 1 kHz; B = 200 Hz | | 2 | 10 | dB |

* Pulse test: t_p ≤ 300μs, δ ≤ 0.02.

■ hFE Classification

| TYPE | BC856 | BC856A | BC856B |
|---------|-------|--------|--------|
| Marking | 3D | 3A | 3B |

| TYPE | BC857 | BC857A | BC857B | BC857C |
|---------|-------|--------|--------|--------|
| Marking | 3H | 3E | 3F | 3G |

| TYPE | BC858B |
|---------|--------|
| Marking | 3K |